



Single Phase Diode Bridge KBPC6



Key Parameters

I_O	=	3	A
V_{RRM}	=	50 - 1000	V
I_{FSM}	=	125	A
I^2t	=	78	A^2s

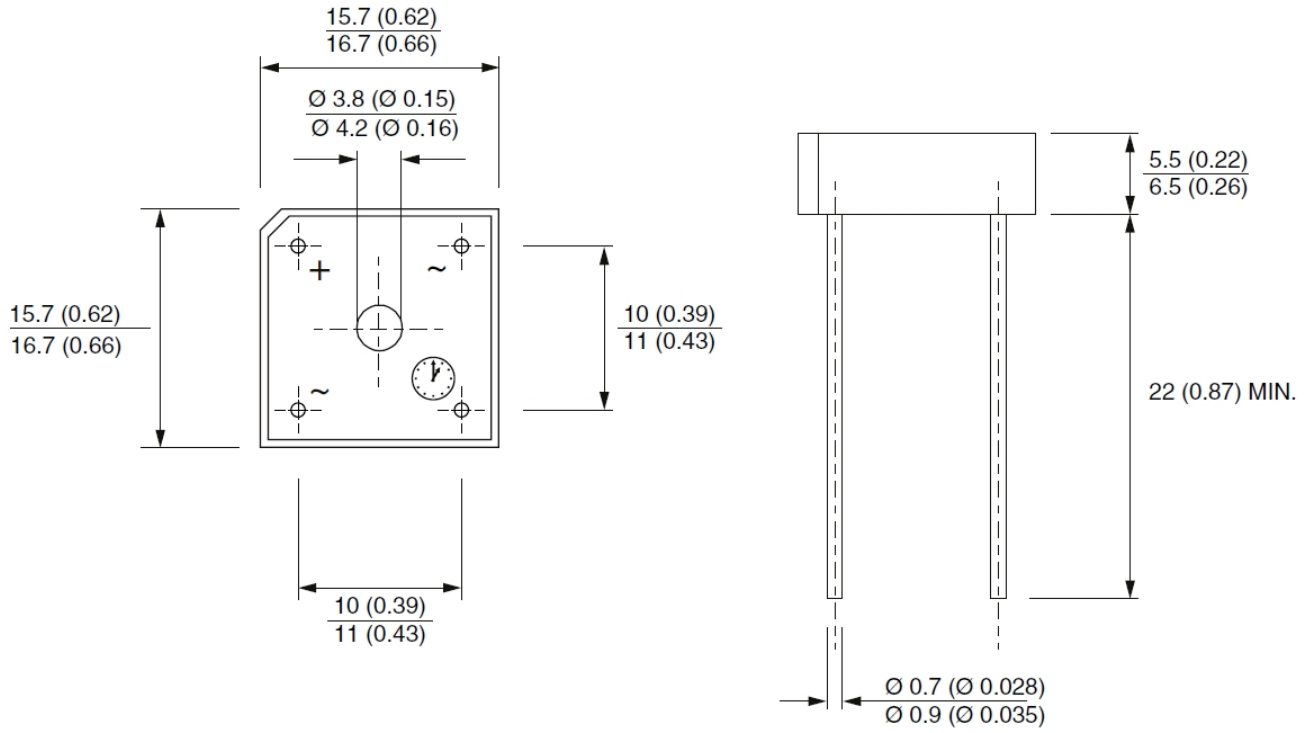
Properties

- Compact construction
- High surge current capability
- Low reverse leakage current
- Low power loss, high efficiency

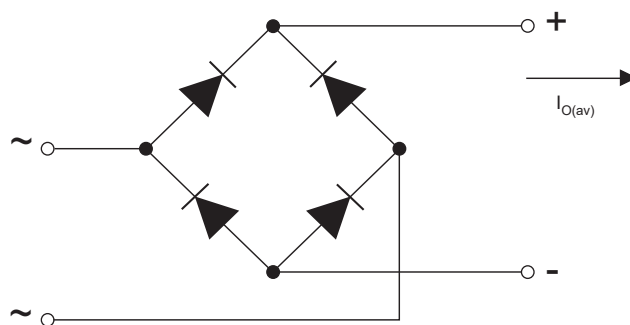
MAXIMUM ALLOWABLE RATINGS AND ELECTRICAL CHARACTERISTICS

Symbols, parameters and values									Unit
V_{RRM}	Repetitive peak reverse voltage	50	100	200	400	600	800	1000	V
I_O	Average rectified output current	Resistive load, $T_C = 50\text{ }^\circ\text{C}$ Capacitive load, $T_C = 50\text{ }^\circ\text{C}$						6	A
								4.7	A
I_{FSM}	Non repetitive peak forward surge current	50 Hz 60 Hz						125	A
								137	A
V_{FM}	Forward voltage per leg	$I_{FM} = 3\text{ A}$						1.2	V
I_{RM}	Typical peak reverse leakage per diode	$T_C = 25\text{ }^\circ\text{C}$ $T_C = 150\text{ }^\circ\text{C}$						10	μA
								1.0	mA
I^2t	I^2t rating for fusing	50 Hz 60 Hz						78	A^2s
								71	A^2s
W	Weight							6	g
T_j, T_{STG}	Operation and storage temperature range							-40...+150	$^\circ\text{C}$

DIMENSIONS



TOPOLOGY OF INTERNAL CONNECTION



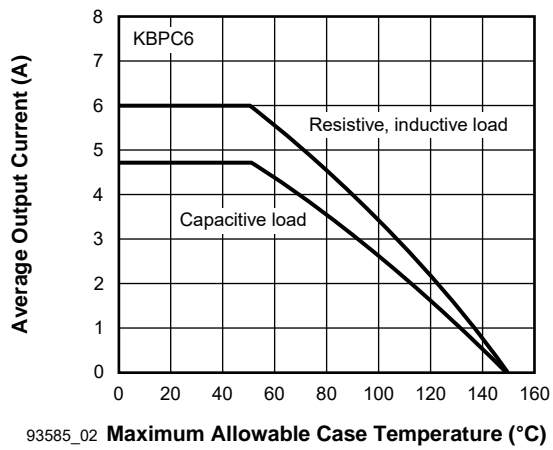


Fig. 2 - Case Temperature Ratings

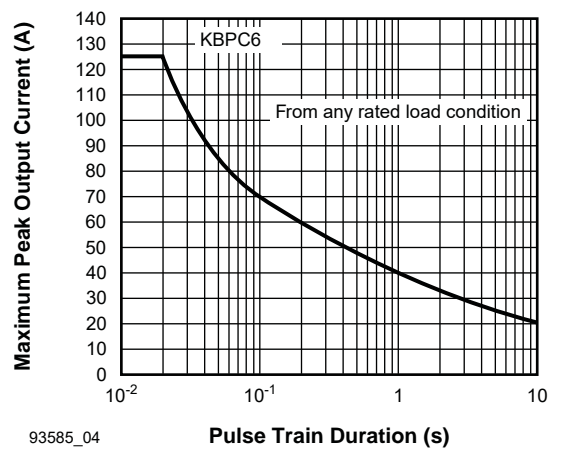


Fig. 4 - Non-Repetitive Surge Ratings